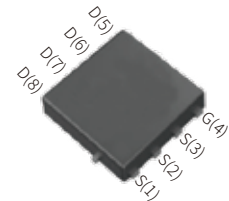


FEATURES

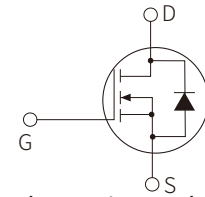
- | Surface-mounted package
- | Advanced trench cell design
- | Super Trench



PDFN5×6-8L

APPLICATION

- | BMS
- | Drones
- | High power inverter system
- | Light electric vehicles



Schematic Symbol

APPROVALS

RoHS	Compliance with 2011/65/EU
HF	Compliance with IEC61249-2-21:2003

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	150	V
Drain Current (Pulsed) $T_c=25^{\circ}\text{C}$	I_{DM}	190	A
Drain Current (DC)	I_D	$T_c=25^{\circ}\text{C}$ 47.8	A
		$T_c=100^{\circ}\text{C}$ 30	A
Gate-Source Voltage	V_{GS}	± 20	V
Drain power dissipation $T_c=25^{\circ}\text{C}$	P_{tot}	62.5	W
Continuous-Source Current $T_c=25^{\circ}\text{C}$	I_S	47.8	A
Single Pulsed Avalanche Energy $L=1.0\text{mH}$	E_{AS}	420	mJ
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}\text{C}$
Thermal Resistance –Junction to Ambient	$R_{\theta JA}^*$	58	$^{\circ}\text{C/W}$
Thermal Resistance- Junction to Case	$R_{\theta JC}$	2	$^{\circ}\text{C/W}$

Notes:

* Surface Mounted on 1 in² pad area, $t \leq 10$ sec

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_{DS}=250\mu A$	150			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2		4	V
Drain Leakage Current	I_{DSS}	$V_{DS}=120V, V_{GS}=0V$			1	μA
Gate Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
On-State Resistance	$R_{DS(on)}^a$	$V_{GS}=10V, I_{DS}=30A$		9.5	11	m Ω
		$V_{GS}=6V, I_{DS}=20A$		11.3	14	m Ω
Diode Characteristics						
Diode Forward Voltage	V_{SD}^a	$I_{SD}=30A, V_{GS}=0V$			1.3	V
Reverse Recovery Time	t_{rr}	$I_{DS}=30A, V_{GS}=0V$ $di_{SD}/dt=100A/\mu s$		81		ns
Reverse Recovery Charge	Q_{rr}			233		nC
Dynamic Characteristics ^b						
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=75V,$ Frequency = 1 MHz		3462		pF
Output capacitance	C_{oss}			213		pF
Reverse transfer capacitance	C_{rss}			14		pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=75V, V_{GEN}=10V$ $R_G=3.9\Omega, R_L=2.5\Omega,$ $I_{DS}=30A$		14		nS
Turn-on Rise Time	t_r			27		nS
Turn-Off Delay Time	$t_{d(off)}$			39		nS
Turn-Off Fall Time	t_f			18		nS
Gate Charge Characteristics ^b						
Total Gate Charge	Q_g	$V_{DS}=75V, V_{GS}=10V, I_{DS}=30A$		66		nC
Gate-Source Charge	Q_{gs}			20		nC
Gate-Drain Charge	Q_{gd}			18		nC

Notes:

a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

b : Guaranteed by design, not subject to production testing

PARAMETER CHARACTERISTIC CURVE

Figure1: Power Capability

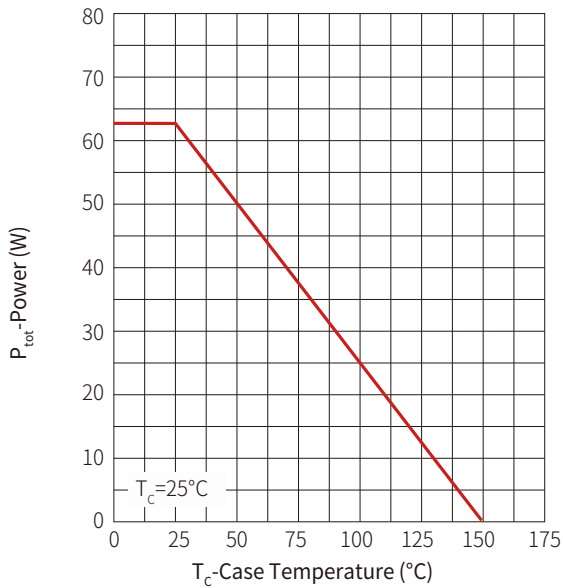


Figure2: Current Capability

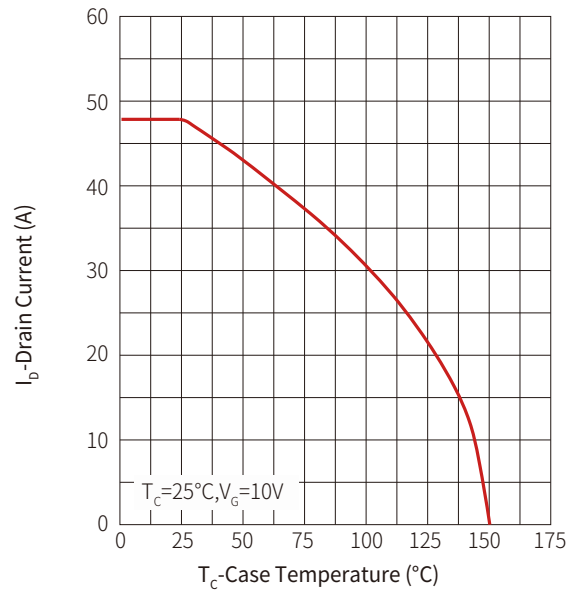


Figure3: Safe operating Area

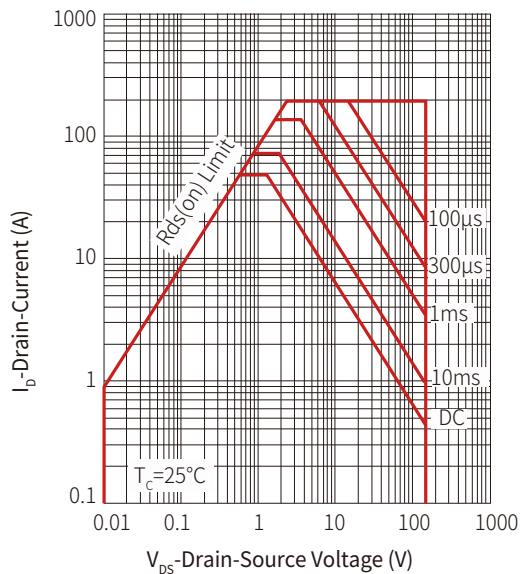


Figure 4: Transient Thermal Impedance

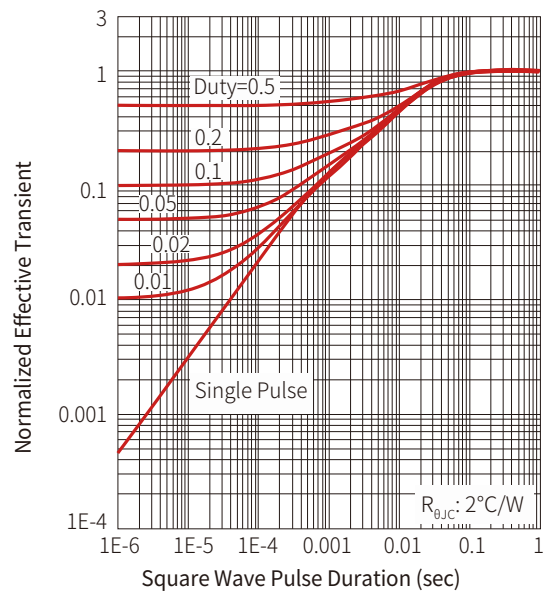




Figure 5: Output Characteristics

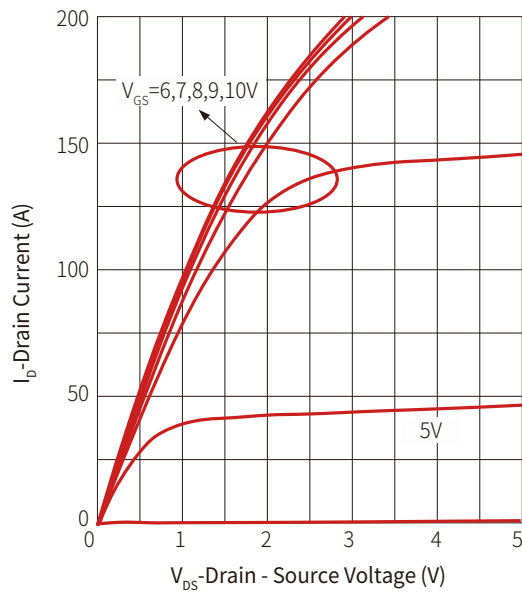


Figure 6: Drain-Source On Resistance

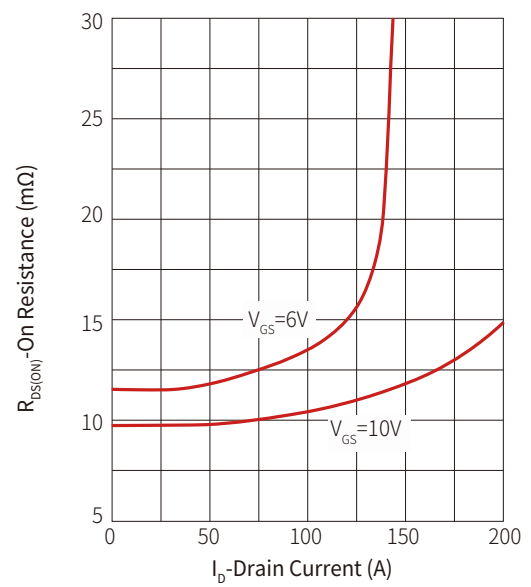


Figure 7: Transfer Characteristics

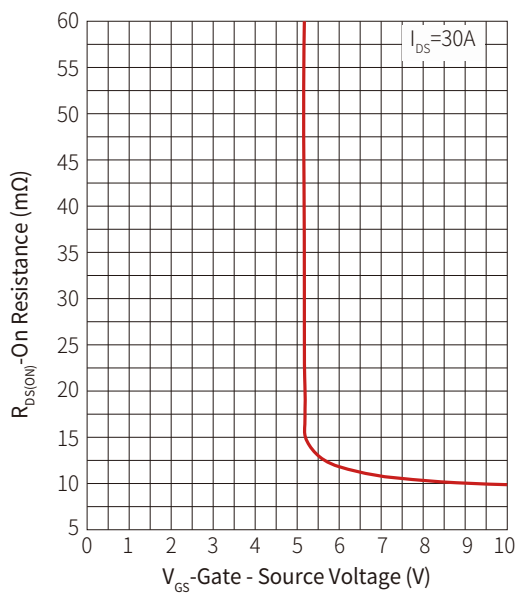


Figure 8: Gate Threshold Voltage

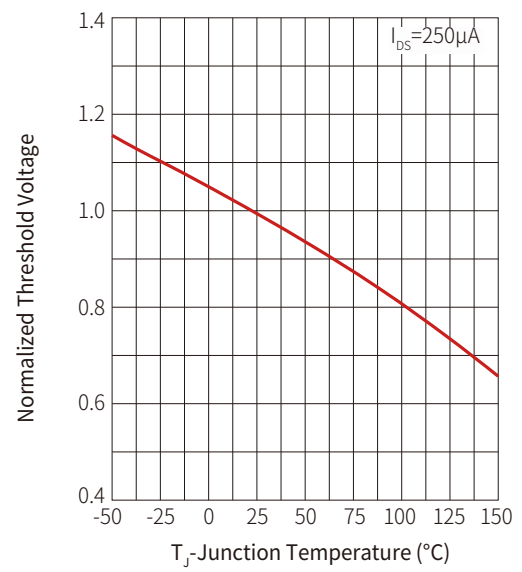
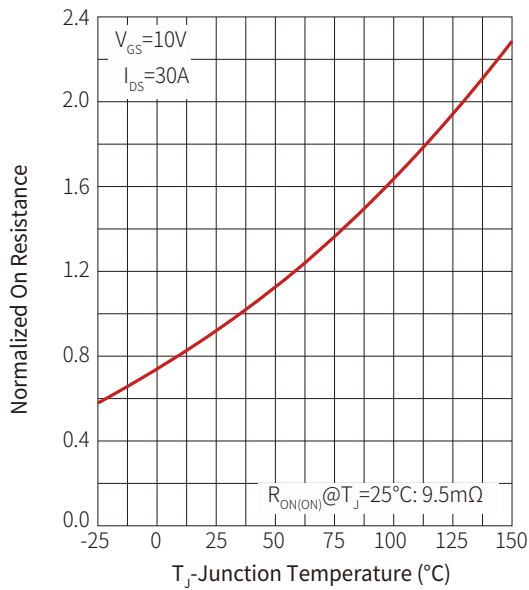
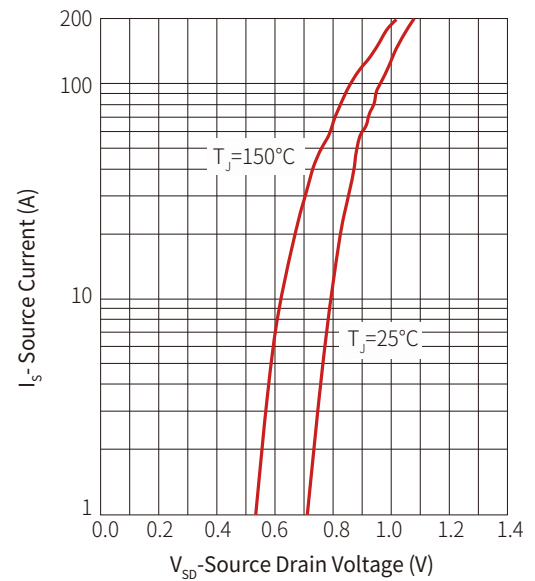
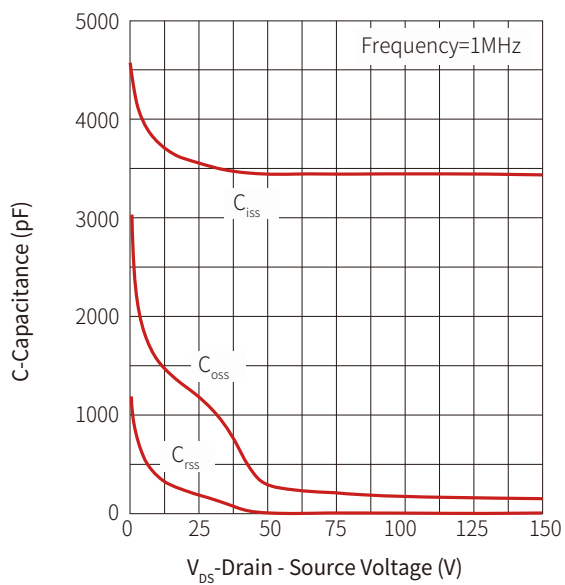
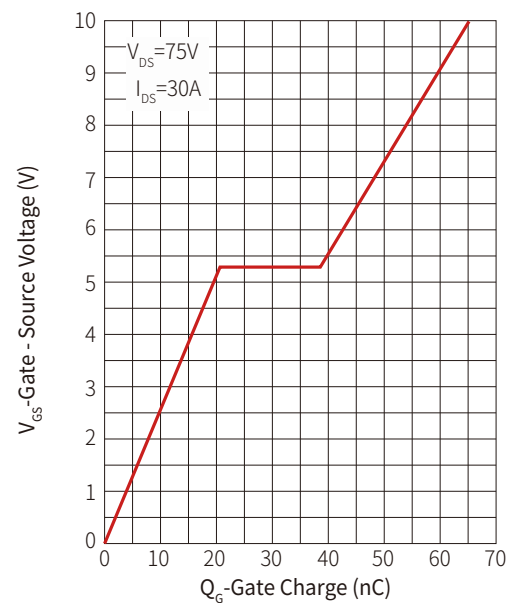


Figure 9: Normalized On Resistance

Figure 10: Body Diode Characteristics

Figure 11: Capacitance

Figure 12: Gate Charge


Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.17	0.035	0.046
A1	0.00	0.05	0.000	0.002
A3	0.254REF		0.010REF	
b	0.31	0.51	0.012	0.020
b1	0.03	0.13	0.001	0.005
b2	0.21	0.41	0.008	0.016
D	5.15BSC		0.203BSC	
D1	5.00BSC		0.197BSC	
D2	3.70	3.90	0.146	0.154
E	6.15BSC		0.242BSC	
E1	6.00BSC		0.236BSC	
E2	3.56	3.76	0.140	0.148
e	1.27BSC		0.050BSC	
L	0.51	0.71	0.020	0.028
M	0.51	0.71	0.020	0.028
P	10°	12°	0.394°	0.472°
aaa	0.10		0.004	
bbb	0.10		0.004	
ccc	0.10		0.004	
ddd	0.05		0.002	
eee	0.08		0.003	

Part Number	Component Package	Marking	QTY/Reel	Reel Size
SNM110N15G	PDFN5×6-8L	 110N15 XXXX	5000PCS	13"

Headquarters

No.3387 Shendu Road
Pujiang I&E Park
Minhang Shanghai China
201000

Hotline

400-021-5756

Web

<https://www.semiware.com>

Sales Center

Tel: 86-21-3463-7458
Email: sales18@semiware.com

Customer Service

Tel: 86-21-5484-1001
Email: sales17@semiware.com

Technical Support

Tel: 86-21-3463-7654
Email: fae01@semiware.com

Complaint & Suggestions

Tel: 86-21-3463-7172
Ext: 8868
Email: cs03@semiware.com

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